

2SK351

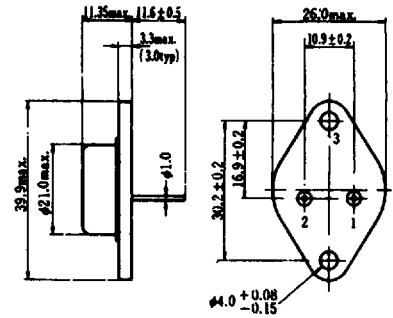
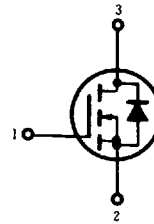
HITACHI/(OPTOELECTRONICS) BLE D

SILICON N-CHANNEL MOS FET

HIGH SPEED POWER SWITCHING,
HIGH FREQUENCY POWER AMPLIFIER

FEATURES

- High Breakdown Voltage.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, RF Amplifiers, and Ultrasonic Power Oscillators.



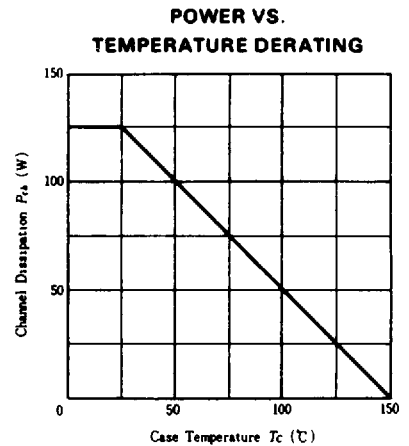
1. Gate
 2. Source
 3. Drain
- (Case)

(Dimensions in mm)

(JEDEC TO-3)

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	5	A
Drain Peak Current	$I_{D(\text{peak})}$	10	A
Body-Drain Diode Reverse Drain Current	I_{DR}	5	A
Channel Dissipation	P_{ch}^*	125	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

*Value at $T_r=25^\circ\text{C}$


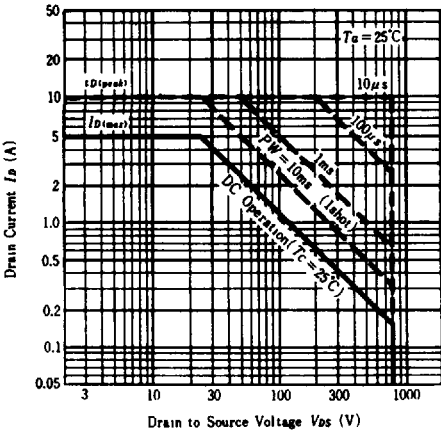
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$I_D=10\text{mA}$, $V_{GS}=0$	800	—	—	V
Gate-Source Leak Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0$	—	—	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=640\text{V}$, $V_{GS}=0$	—	—	1	mA
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$I_D=1\text{mA}$, $V_{DS}=10\text{V}$	1.0	—	5.0	V
Static Drain-Source On State Resistance	$R_{DS(on)}$	$I_D=3\text{A}$, $V_{GS}=15\text{V}^*$	—	1.7	3.0	Ω
Drain-Source Saturation Voltage	$V_{DS(on)}$	$I_D=3\text{A}$, $V_{GS}=15\text{V}^*$	—	5.0	9.0	V
Forward Transfer Admittance	$ y_f $	$I_D=3\text{A}$, $V_{DS}=10\text{V}^*$	1.0	2.0	—	S
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}$, $V_{GS}=0$ $f=1\text{MHz}$	—	1900	—	pF
Output Capacitance	C_{oss}		—	320	—	pF
Reverse Transfer Capacitance	C_{rss}		—	40	—	pF
Turn-on Delay Time	t_{don}	$I_D=2\text{A}$, $V_{GS}=15\text{V}$ $R_L=15\Omega$	—	30	—	ns
Rise Time	t_r		—	70	—	ns
Turn-off Delay Time	t_{doff}		—	220	—	ns
Fall Time	t_f		—	80	—	ns
Body-Drain Diode Forward Voltage	V_{DF}	$I_F=3\text{A}$, $V_{GS}=0$	—	0.8	—	V
Body-Drain Diode Reverse Recovery Time	t_{rr}	$I_F=3\text{A}$, $V_{GS}=0$ $di_F/dt=100\text{A}/\mu\text{s}$	—	600	—	ns

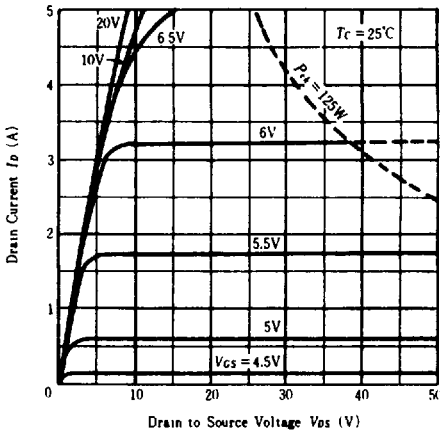
*Pulse Test

HITACHI/(OPTOELECTRONICS)

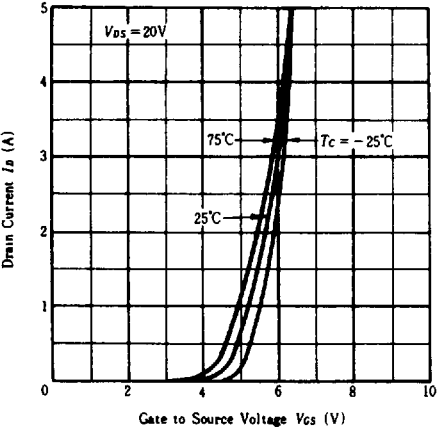
MAXIMUM SAFE OPERATION AREA



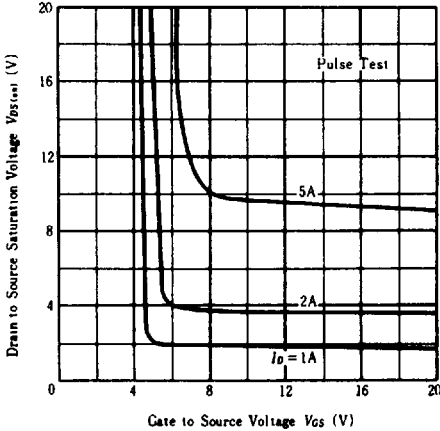
TYPICAL OUTPUT CHARACTERISTICS



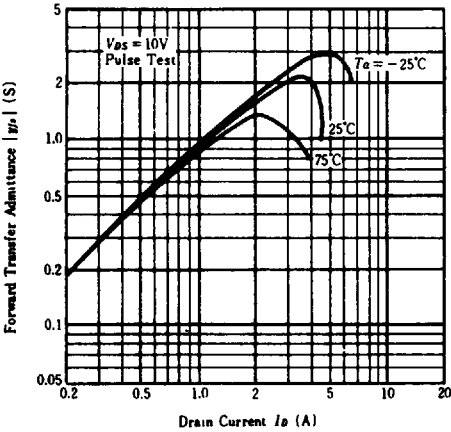
TYPICAL TRANSFER CHARACTERISTICS



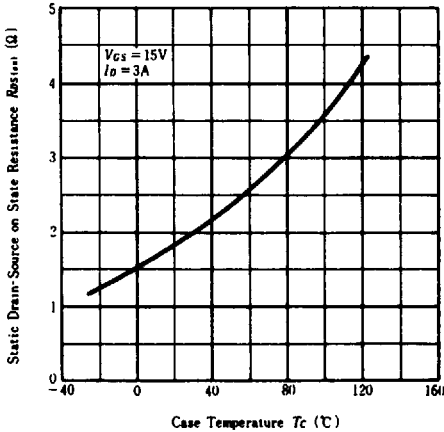
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



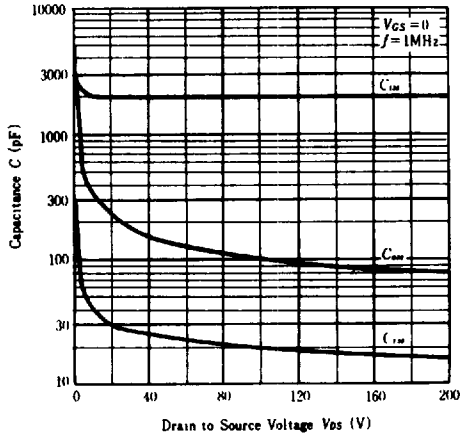
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT



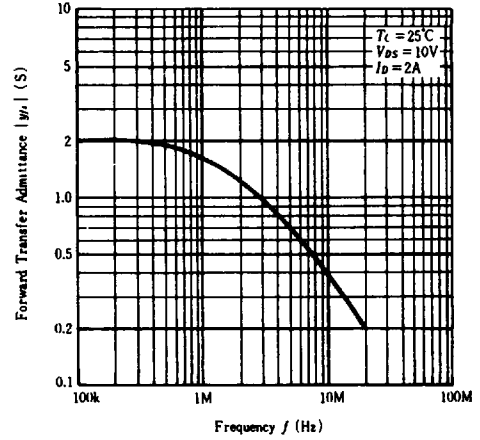
STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE



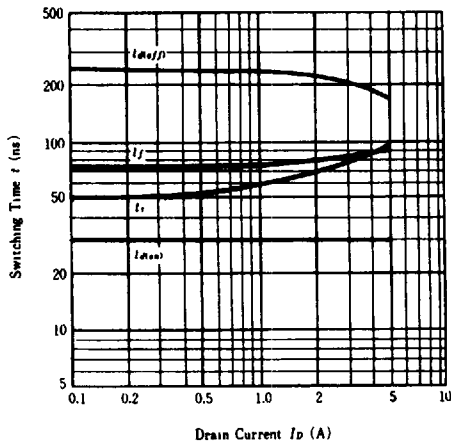
**TYPICAL CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE**



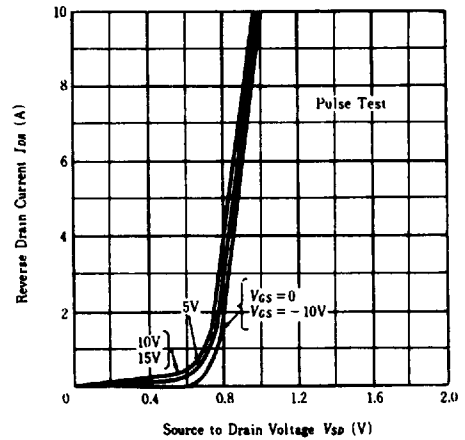
**FORWARD TRANSFER ADMITTANCE
VS. FREQUENCY**



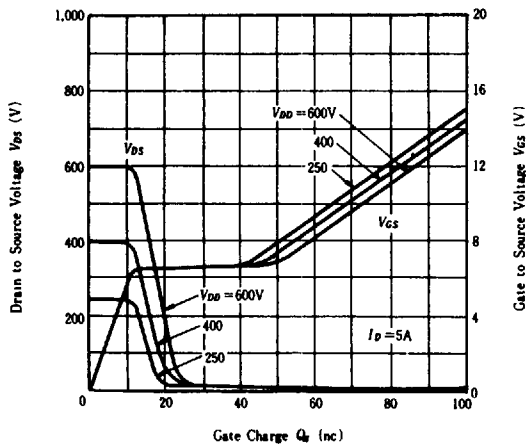
SWITCHING CHARACTERISTICS



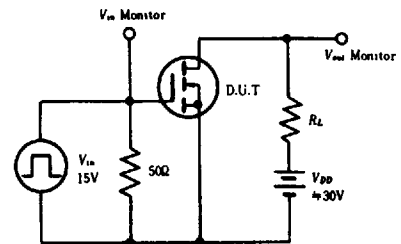
**MAXIMUM BODY-DRAIN DIODE
FORWARD VOLTAGE**



DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT



WAVEFORMS

